



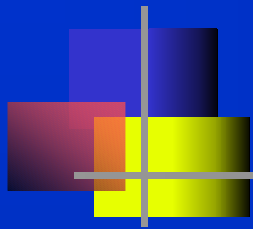
# *Study on microprobe processing by LIGA on Si*

*Fundamental study for 3-D mold -Report 1-*

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*A potential new technology for  
probing super-fine-pitch LCD  
drivers with Au bumps*



# *Outline*

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- *Introduction*
- *Experimental Procedures*
- *Results*
- *Conclusions*

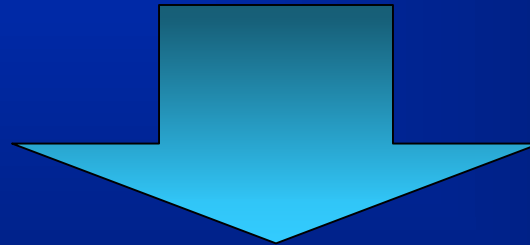


# *Background*

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## *Problem*

Conventional cantilever probe cards may not achieve the pitch requirement in the near future.



## *Need*

New fabrication process to achieve the finer pitch probing.



# *LIGA Features*

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*LIGA : Lithographie, Galvanoformung und Abformung*

- High aspect ratio :  $> 20$
- High accuracy :  $< 0.5 \text{ um}$
- High uniformity



# *Purpose*

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## Requirements for probing LCD drivers

- Fine pitch ( < 35um )
- Good contact with gold bump
- Minimal bump damage
- Low cost



# *Concept of 3-D Micro Probe Processing*

## LIGA process

- Pros  
High aspect ratio & High accuracy
- Con  
High processing cost per mask

## Si anisotropic etching

- Pro  
Can form sloped shape with only 1 standard UV mask
- Con  
Limit on probe tip shape

## Combination

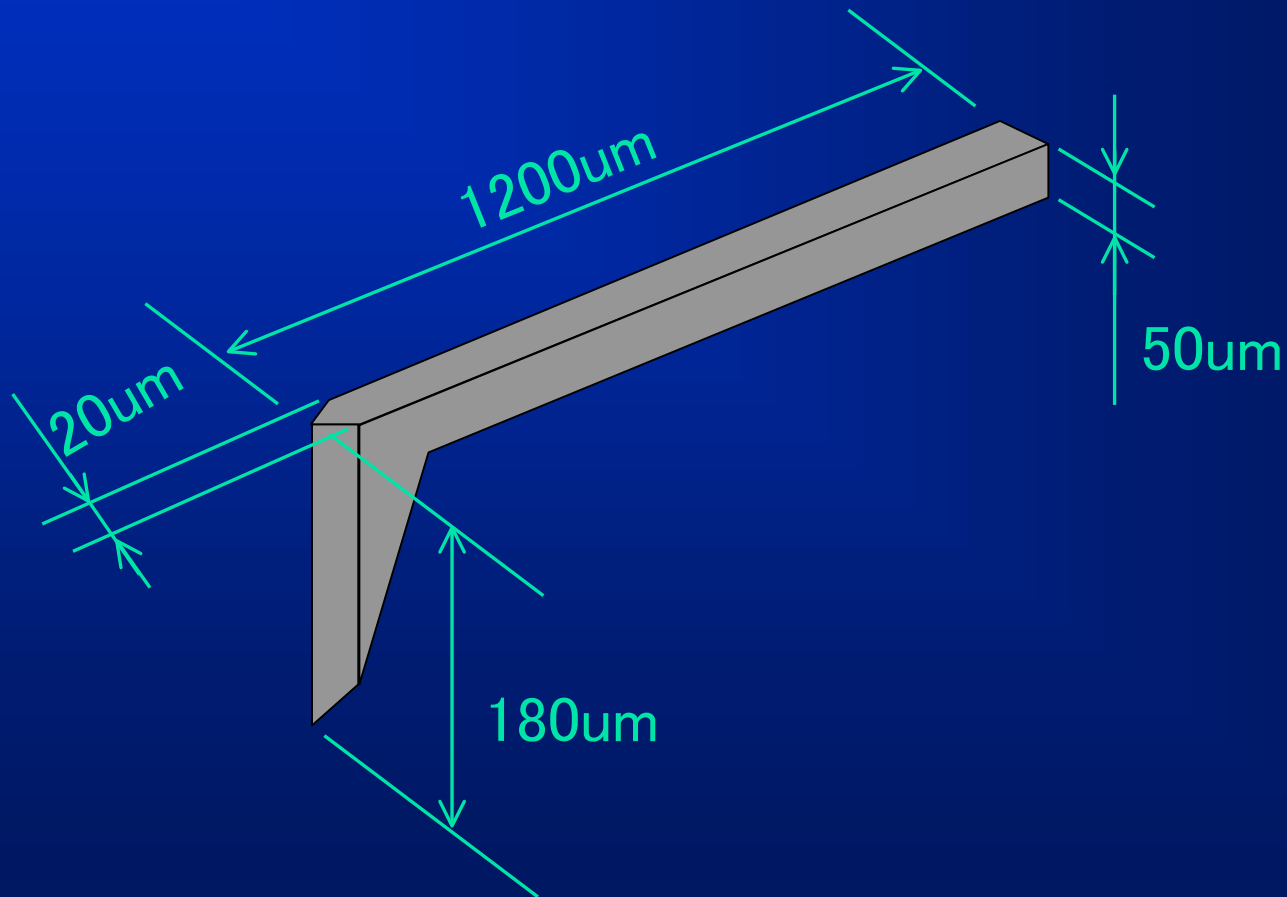
3-D micro probe



# *Design target of 3-D probe*

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Probe model by Ni electroforming

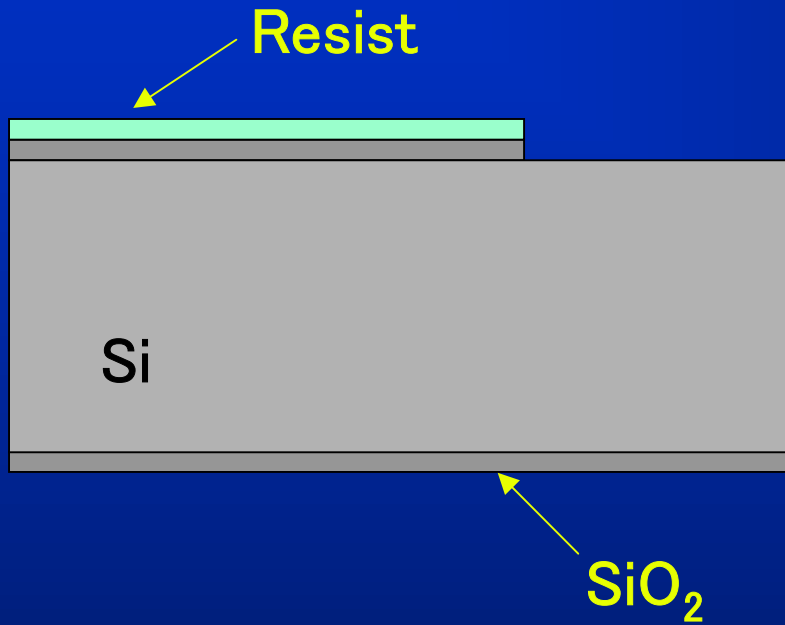




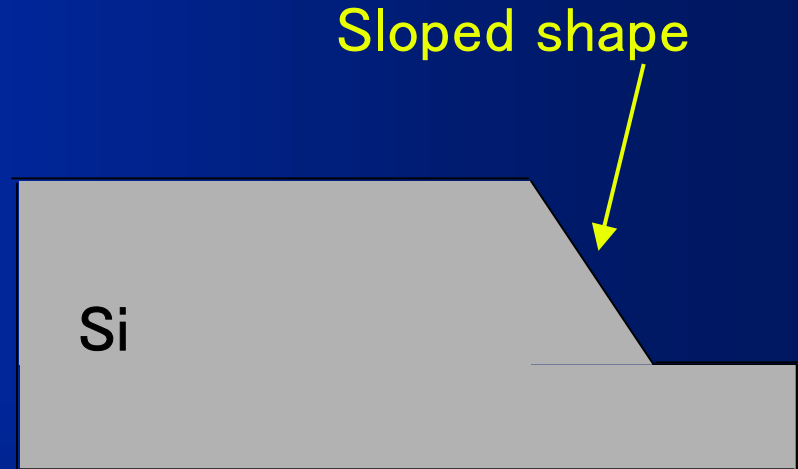


# *Process concept*

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Preparation for etching

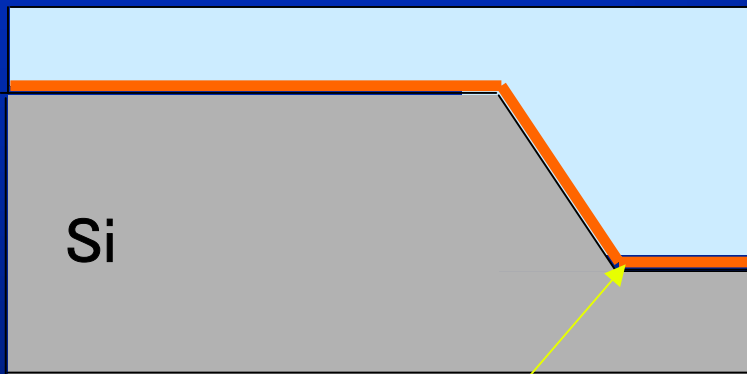


Si anisotropic etching

# Process concept

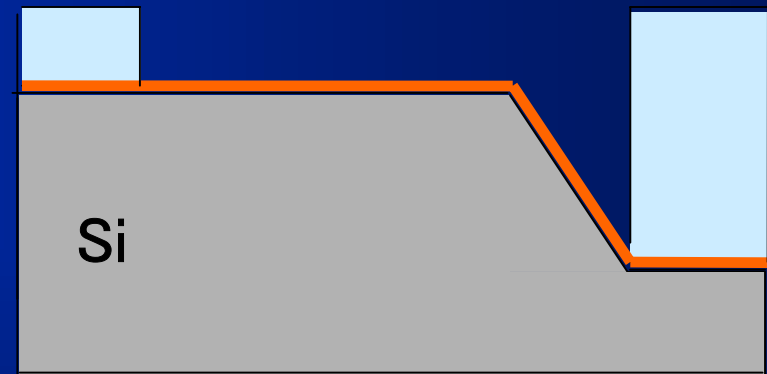
## X-ray lithography

Thick resist



Plating seed layer

Thick resist preparation

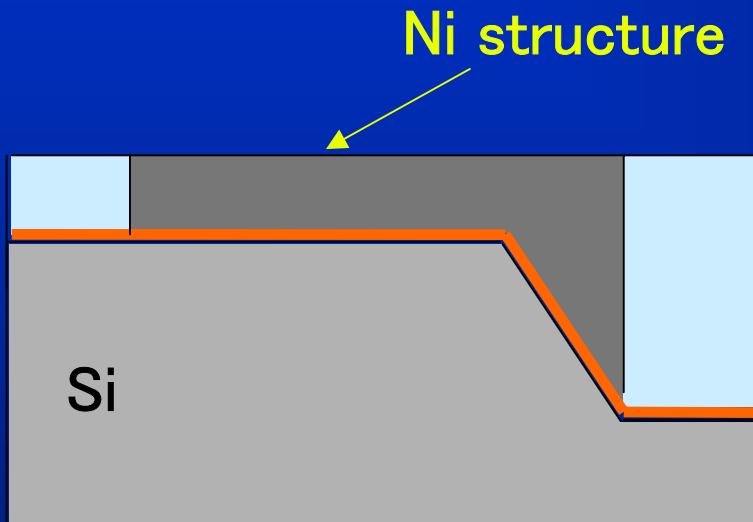


X-ray lithography

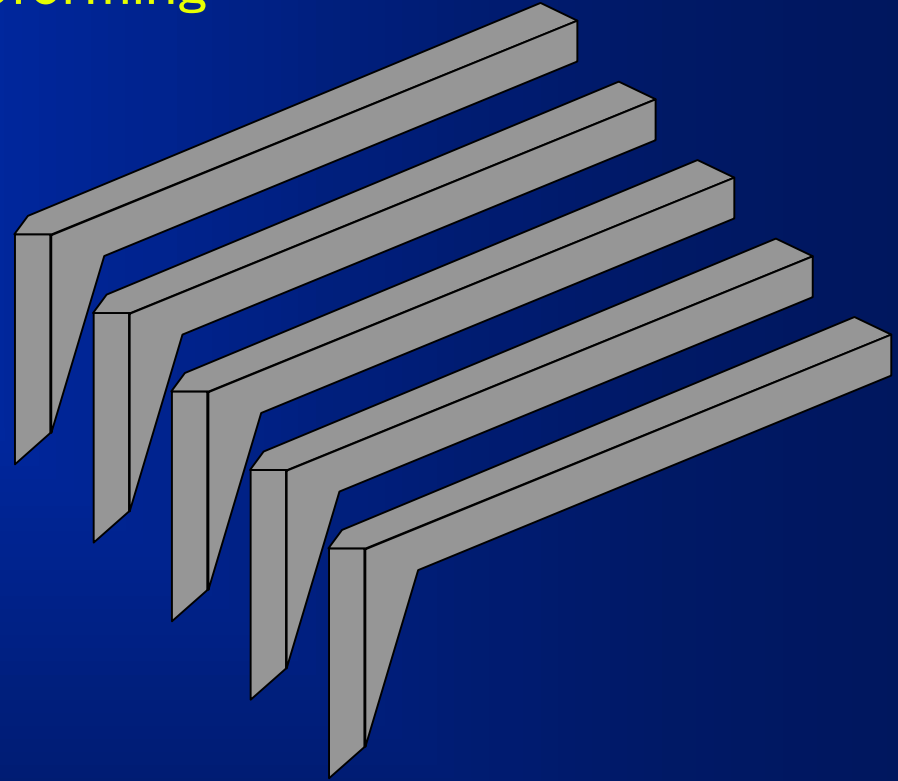


# Process concept

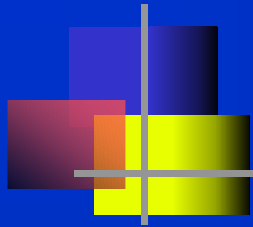
## Ni electroforming



Ni electroforming



Resist and substrate removal

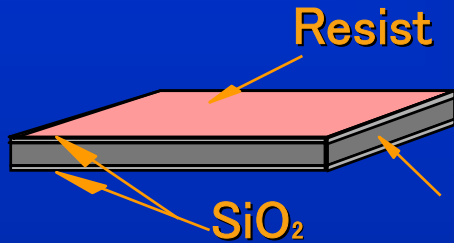


## *Experimental procedures*

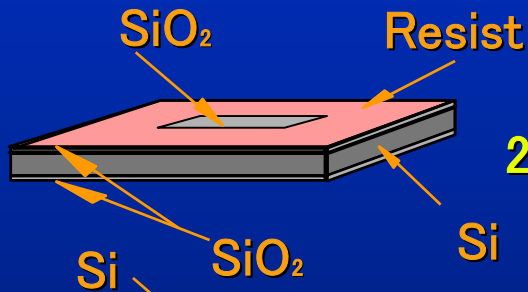
- Si anisotropic etching
- X-Ray lithography
- Ni electroforming & Lapping

# Si anisotropic etching

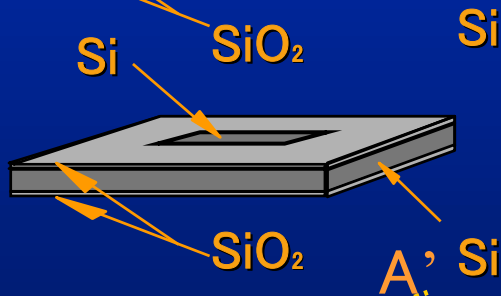
Slope formation for 3-D mold



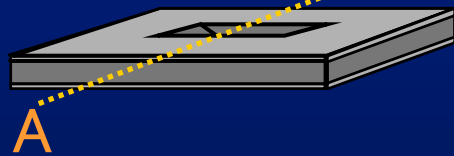
1. Photo resist formation



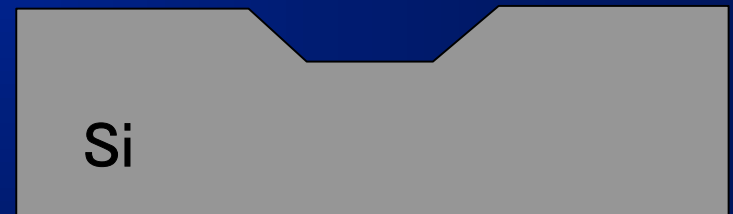
2. UV lithography



3. SiO<sub>2</sub> layer removal



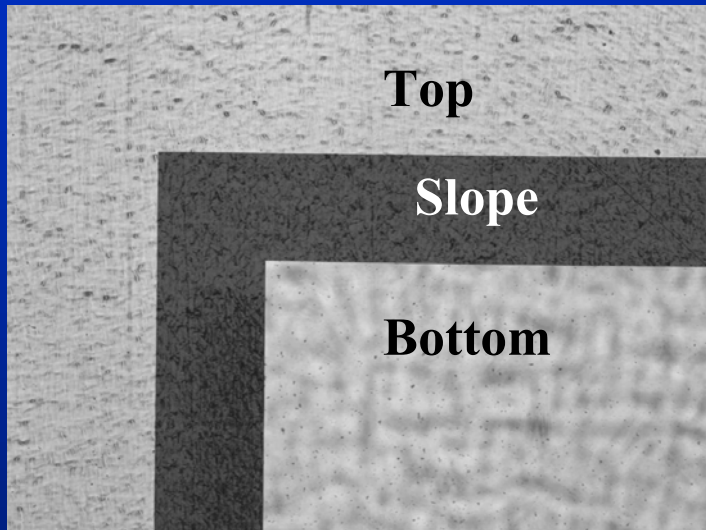
4. Si anisotropic etching



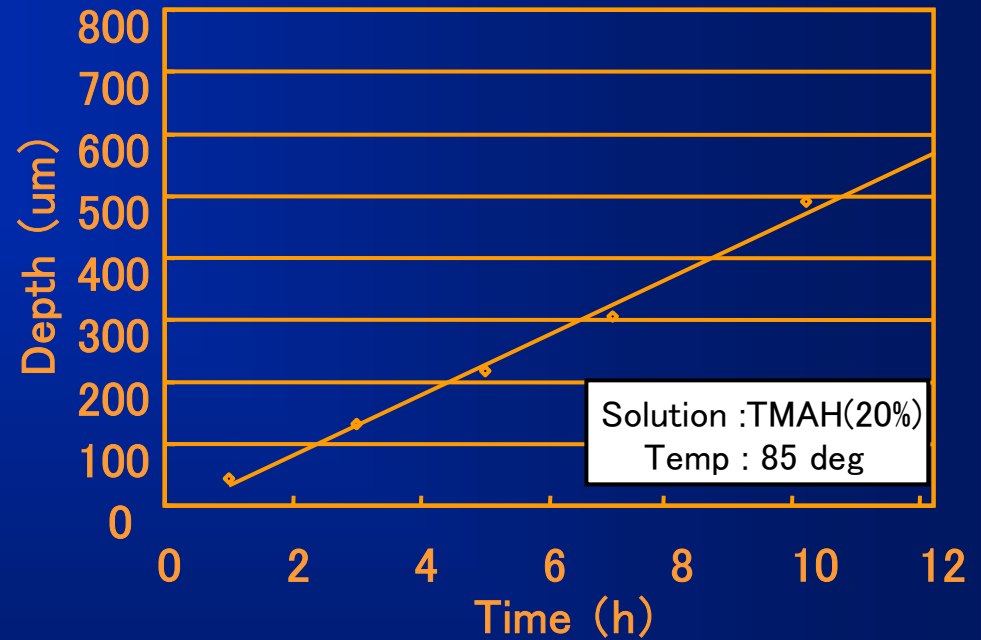
Cross section of A-A'

Process step of Si anisotropic etching

# Si anisotropic etching



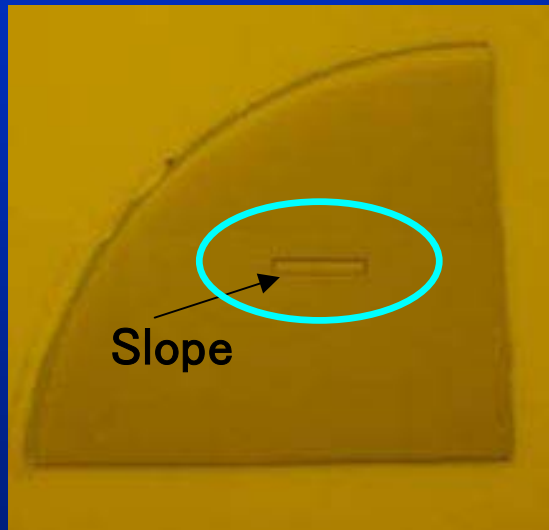
Photograph of slope



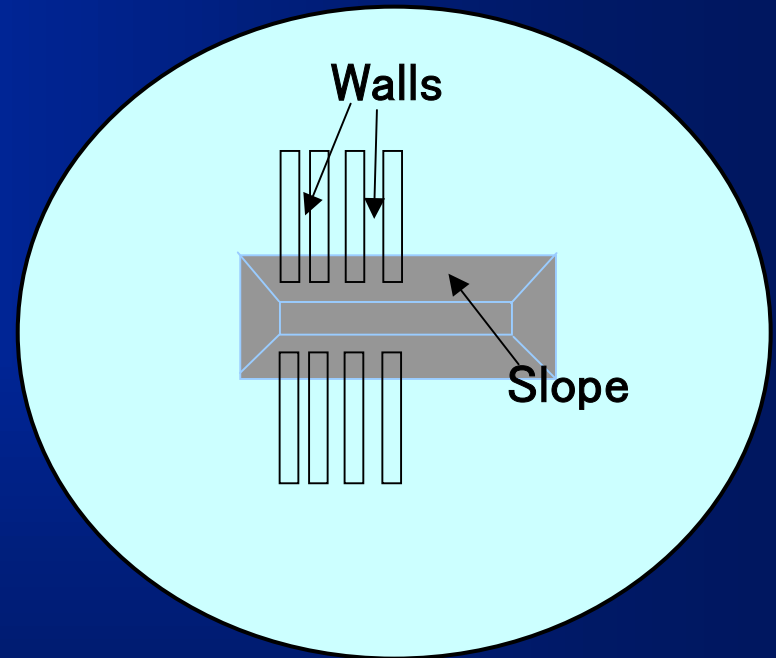
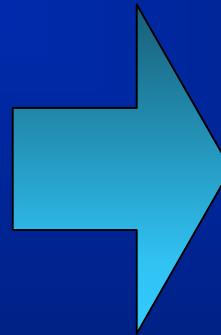
Etching rate

# X-ray lithography

## Thick resist preparation on mold

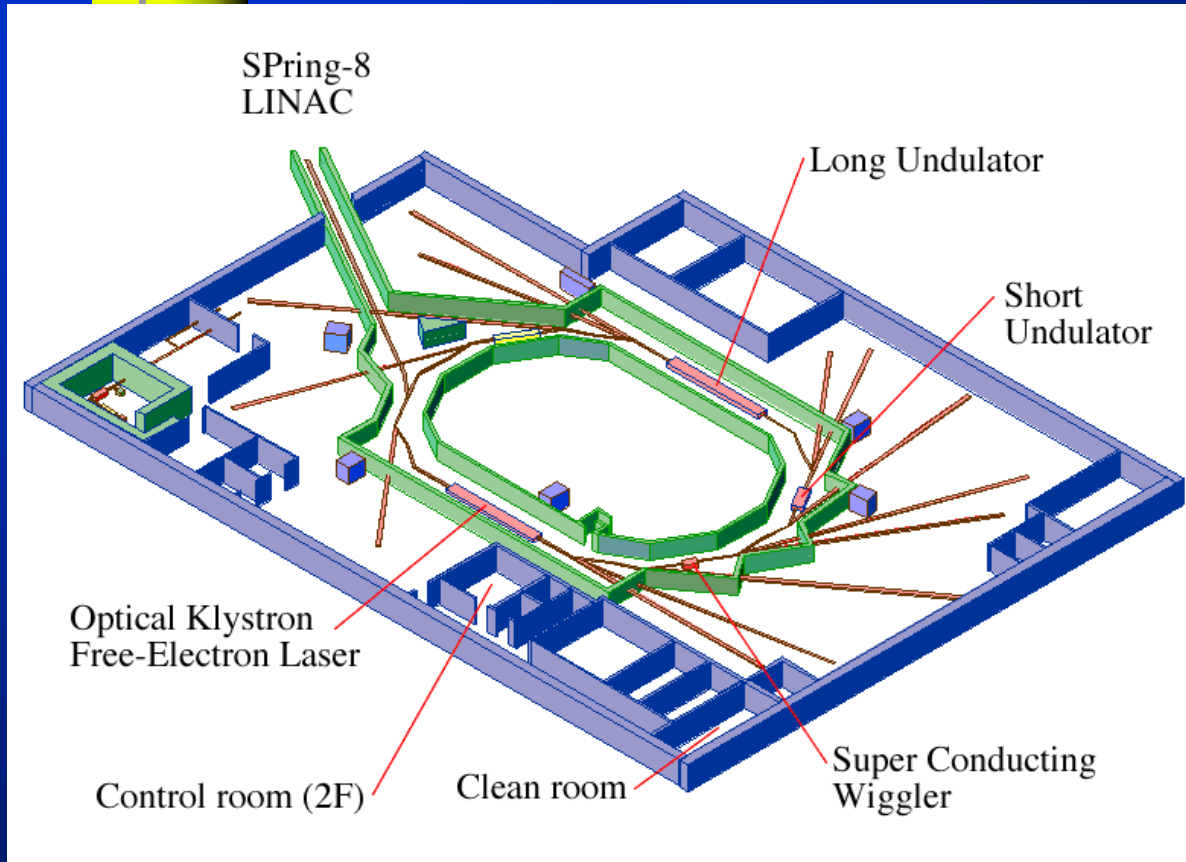


Photograph of substrate



Enlarged view

# X-ray lithography



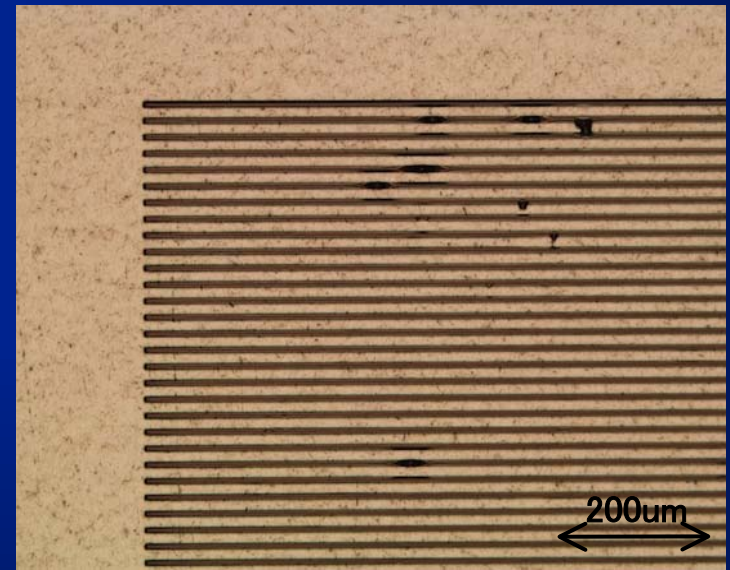
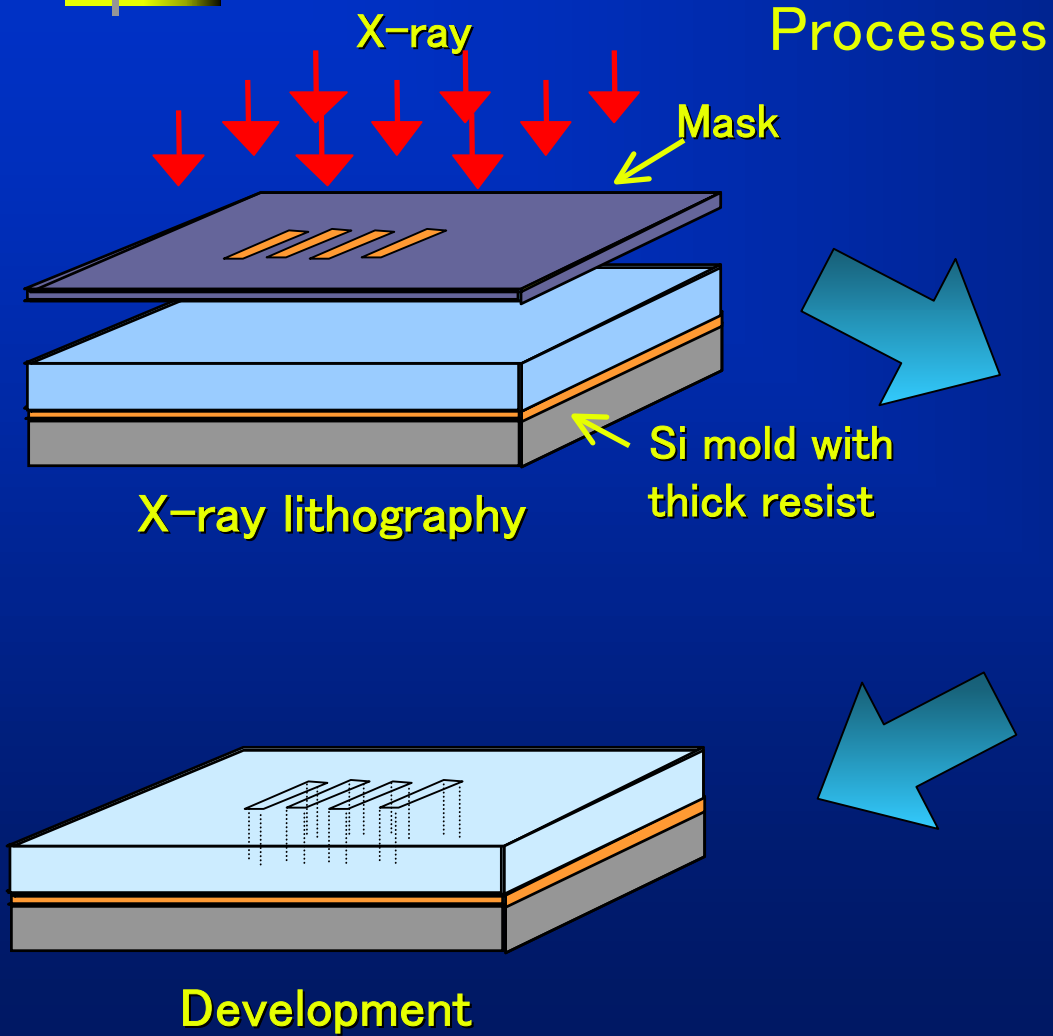
## New Subaru Radiation Facility

## Characteristics of X-ray lithography

Wavelength	0.1-1 nm
Storage energy	1.5 GeV



# X-ray lithography

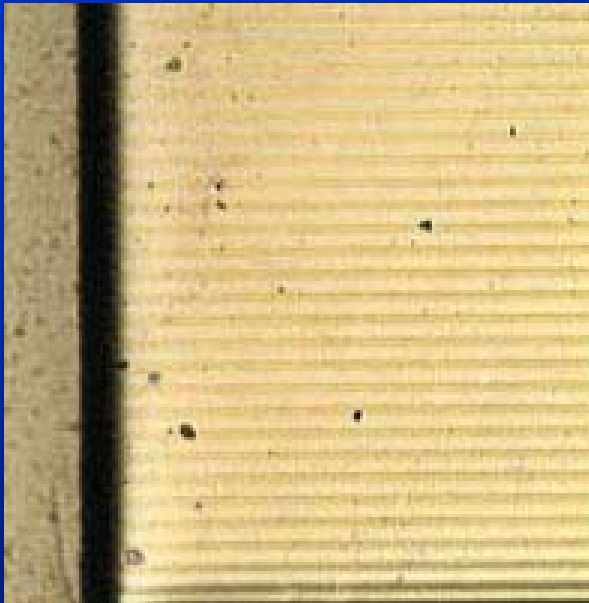


Surface view after lithography

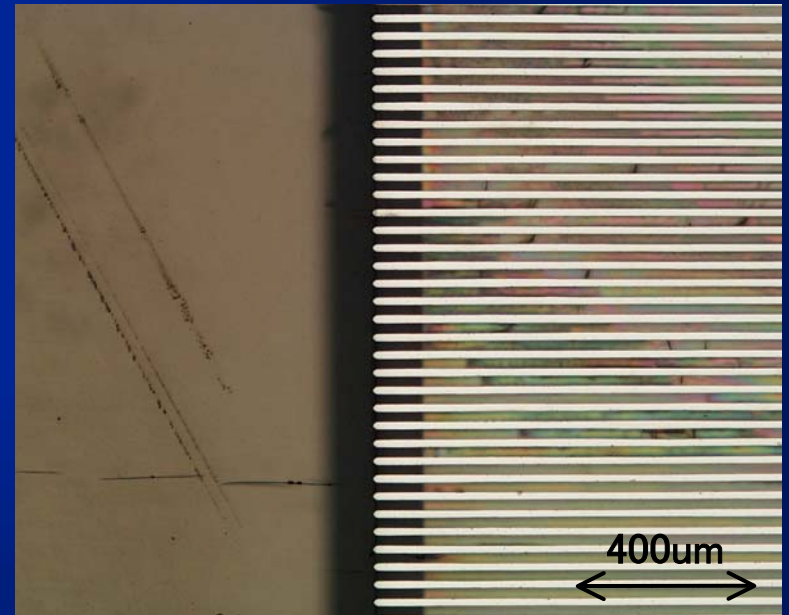


# *Electroforming & lapping*

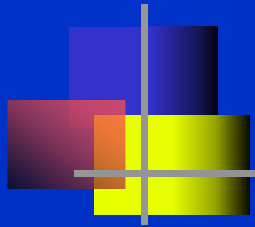
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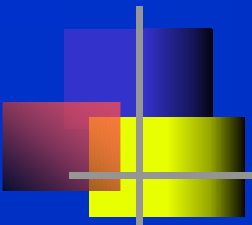
Probe array after  
electroforming



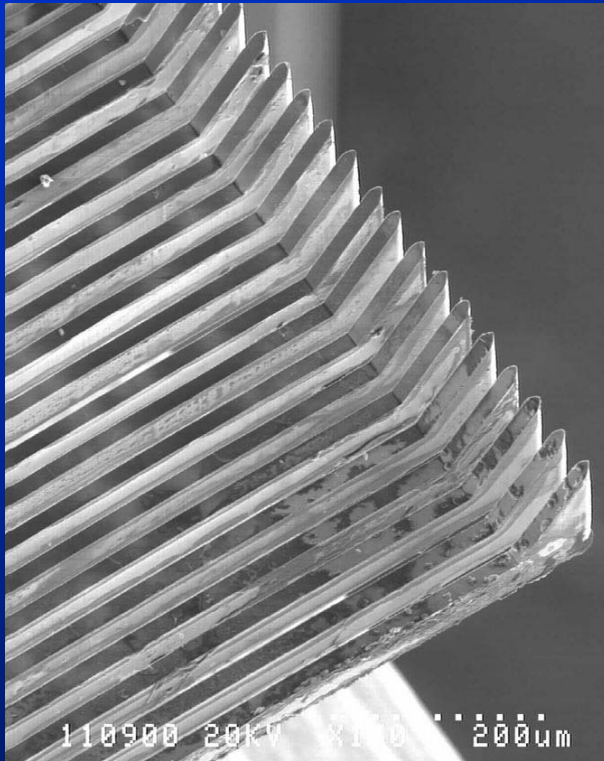
Probe array after lapping



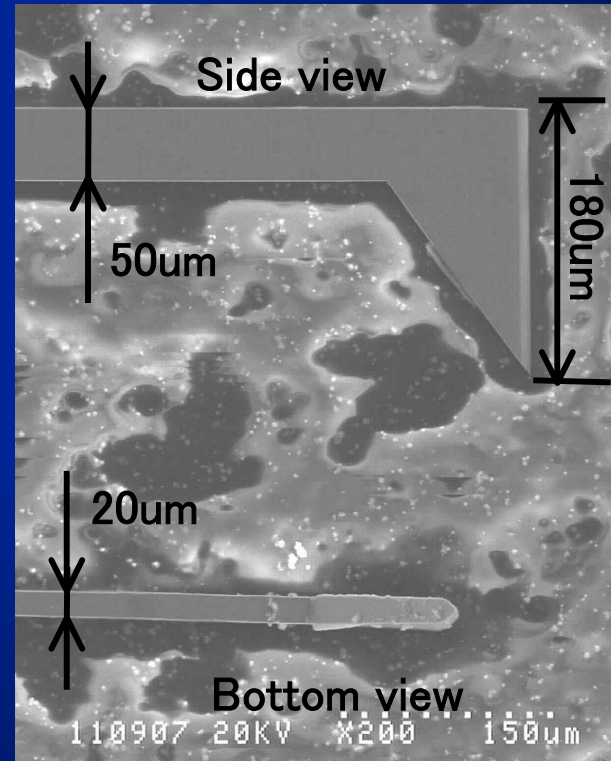
# *Results*



# Probes

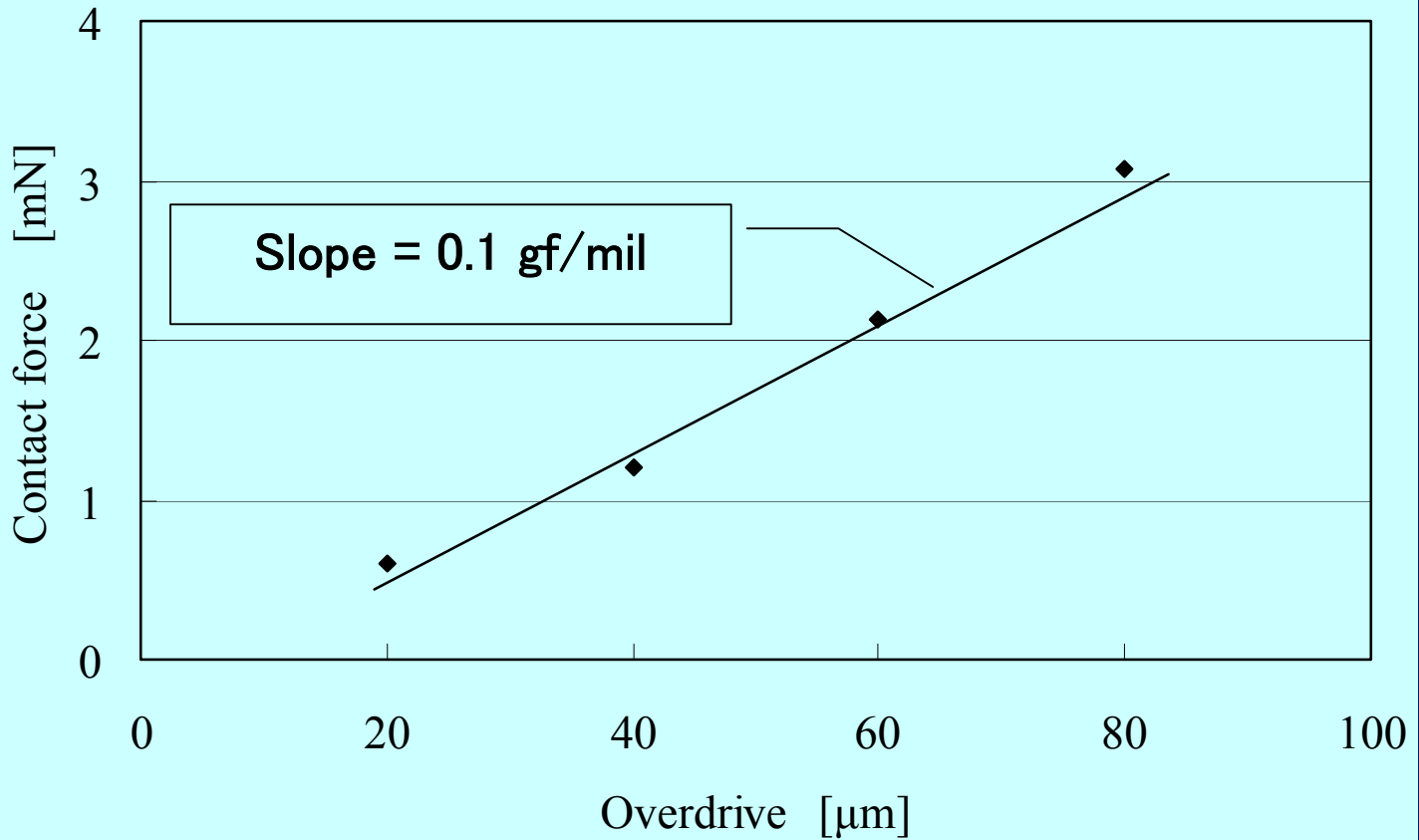


40um pitch

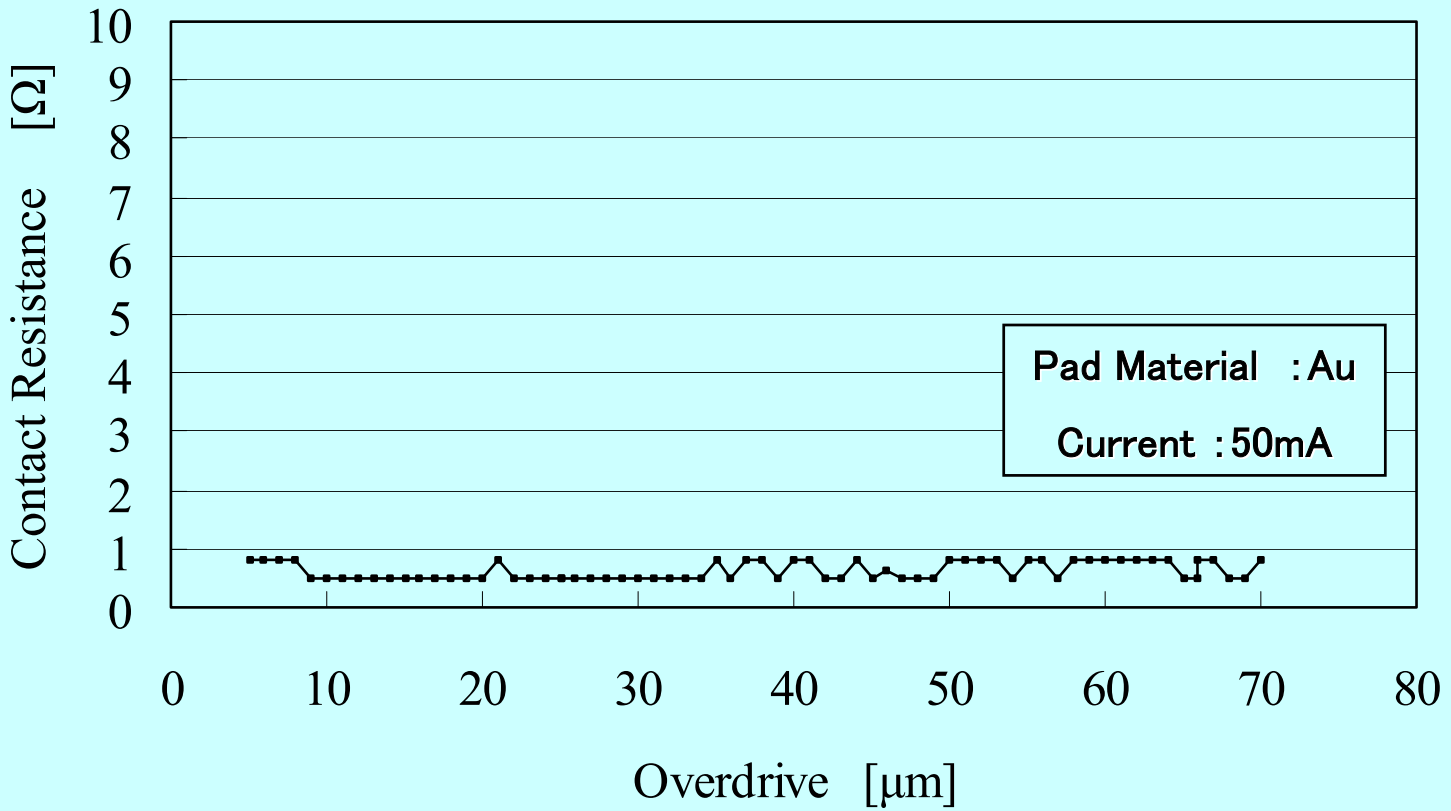


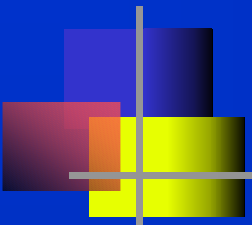
SEM photograph of micro probe

# Contact force vs Overdrive



# Contact resistance vs Overdrive





# *Conclusions*



## *Conclusions*

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1. Micro probe with 3-D shape is manufactured by combining the processes of LIGA and Si anisotropic etching.
2. 80um of allowable probe tip deflection
3. Satisfactory electrical contact within 10um to 70um overdrive can be obtained.
4. 3-D micro probe has the potential to be used for probing super-fine-pitch LCD drivers with gold pads.





## *What are the next steps?*

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### 1. Continue to evaluate the probes

- ◆ Mechanical contact test (scrub, wear)
- ◆ Electrical test (Cres vs. No of touchdowns)
- ◆ Cleaning process and frequency

### 2. Reduce pitch (<25 um)

### 3. Finalize assembly process